ShinDengen

P56LA4SN

Power MOSFETs
40V, 56A, N-channel

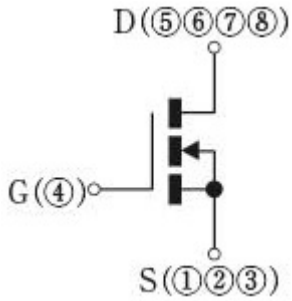
Feature

- N-channel
- Small SMD
- Low Ron
- 10V Gate Drive
- Low Capacitance
- Halogen free
- Pb free terminal
- RoHS:Yes

OUTLINE

Package (House Name): LA

Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25℃)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	℃
Channel tempertature	Tch		-55 to 150	℃
Drain-source voltage	V_{DSS}		40	V
Gate-source voltage	V_{GSS}		±20	V
Continuous drain current(DC)	I_D		56	A
Continuous drain current(Peak)	I_{DP}	Pulse width 10μs, duty=1/100	168	A
Total power dissipation	P_T		99	W
Single avalanche current	I_{AS}	Starting Tch=25℃ Tch≦150℃	28	A
Single avalanche energy	E_{AS}	Starting Tch=25℃ Tch≦150℃	95	mJ

※ :See the original Specifications

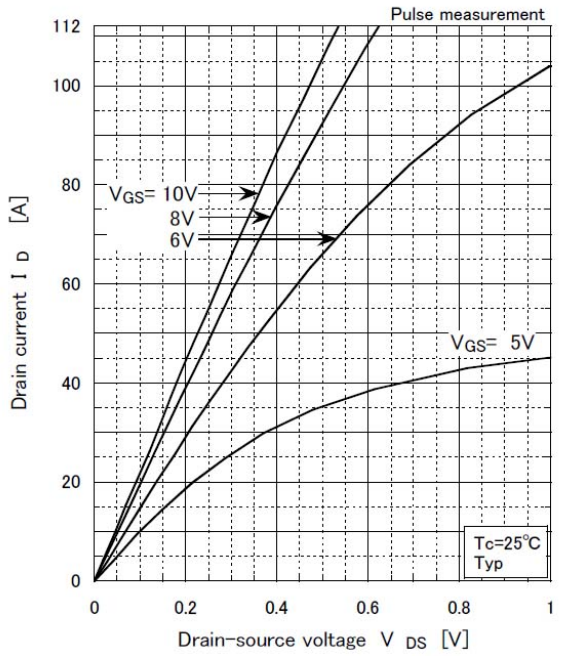
Electrical Characteristics (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	$V_{(BR)DSS}$	ID=1mA, VGS=0V	40			V
Zero gate voltage drain current	I_{DSS}	VDS=40V, VGS=0V			1	μA
Gate-source leakage current	I_{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g_{fs}	ID=28A, VDS=10V	8			S
Static drain-source on-state resistance	$R_{DS(ON)}$	ID=28A, VGS=10V		0.0045	0.0057	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	2	3	4	V
Source-drain diode forward voltage	V_{SD}	IS=56A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case, with heatsink			1.26	°C/W
Total gate charge	Qg	VDD=32V, VGS=10V, ID=56A		38		nC
Gate to source charge	Qgs	VDD=32V, VGS=10V, ID=56A		10		nC
Gate to drain charge	Qgd	VDD=32V, VGS=10V, ID=56A		15		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		1680		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		187		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		335		pF
Turn-on delay time	td(on)	ID=28A, RL=0.7Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		5.4		ns
Rise time	tr	ID=28A, RL=0.7Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		8.6		ns
Turn-off delay time	td(off)	ID=28A, RL=0.7Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		18.6		ns
Fall time	tf	ID=28A, RL=0.7Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		8.2		ns
Diode reverse recovery time	trr	IF=56A, VGS=0V, di/dt=100A/μs		36		ns
Diode reverse recovery charge	Qrr	IF=56A, VGS=0V, di/dt=100A/μs		33		nC

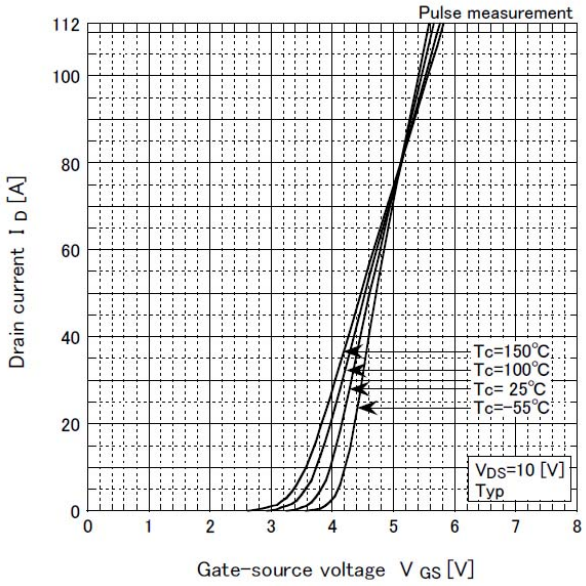
※ ：See the original Specifications

CHARACTERISTIC DIAGRAMS

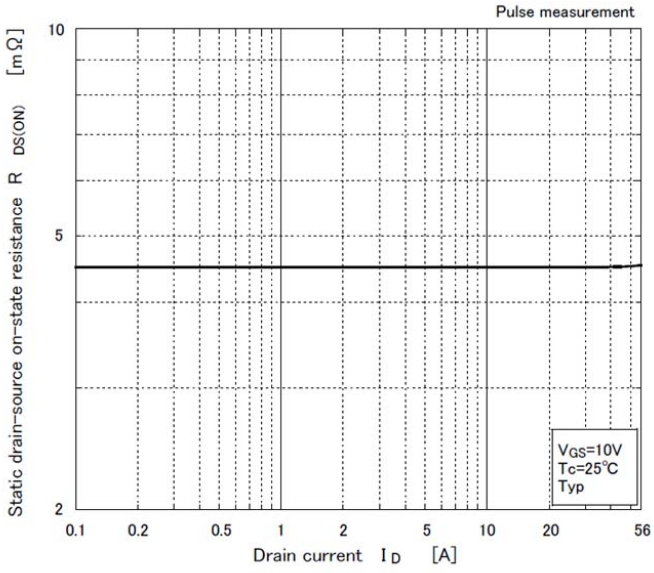
Typical output characteristics

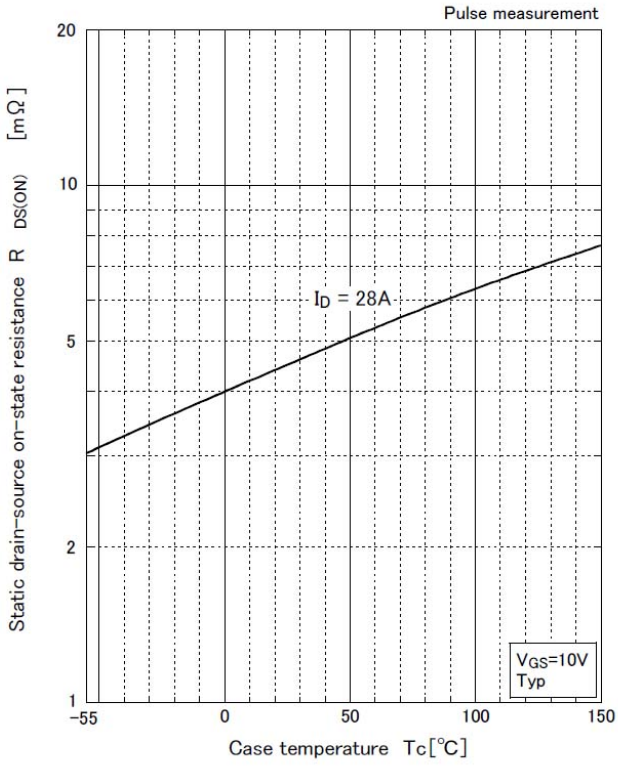


Transfer characteristics

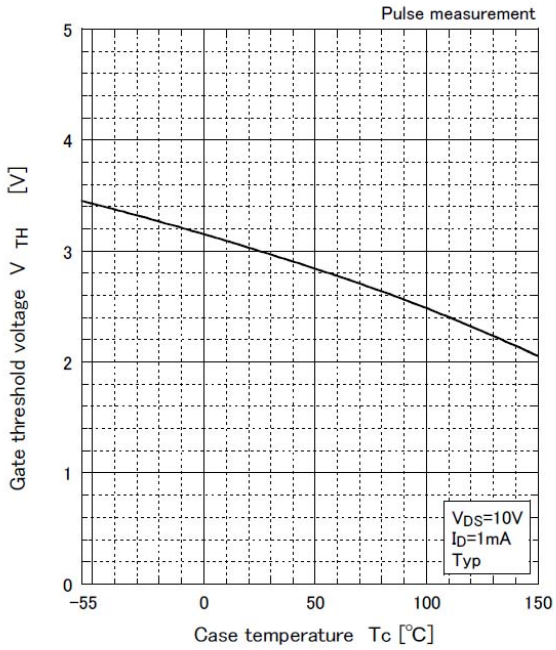


Static drain-source on-state resistance vs drain current

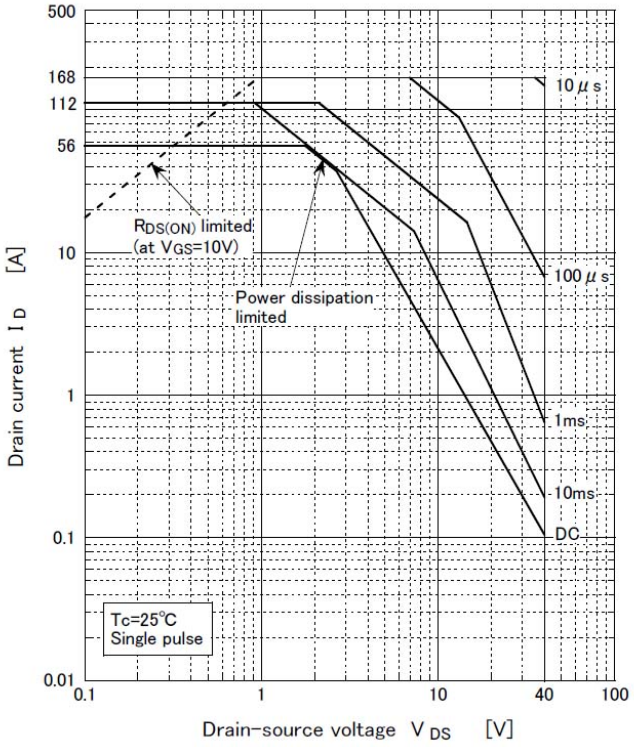


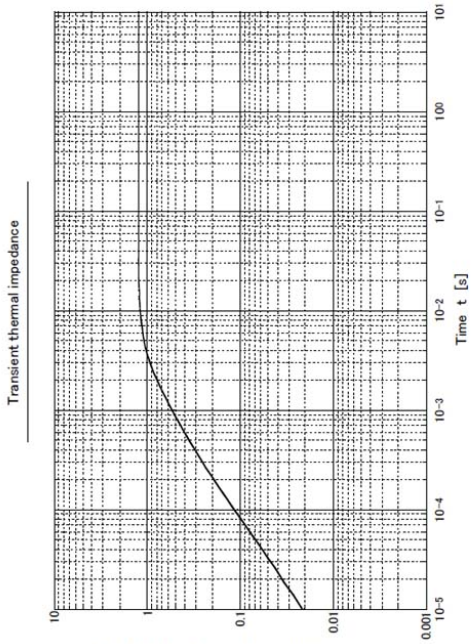


Gate threshold voltage
vs case temperature

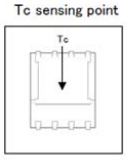


Safe operating area

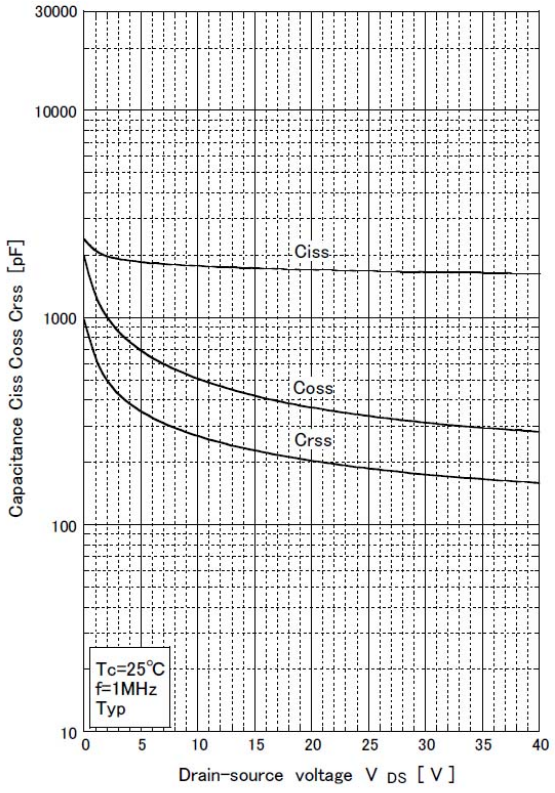




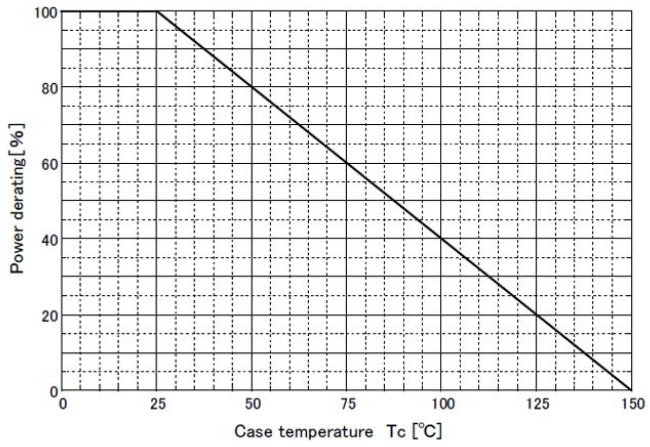
Tc sensing point



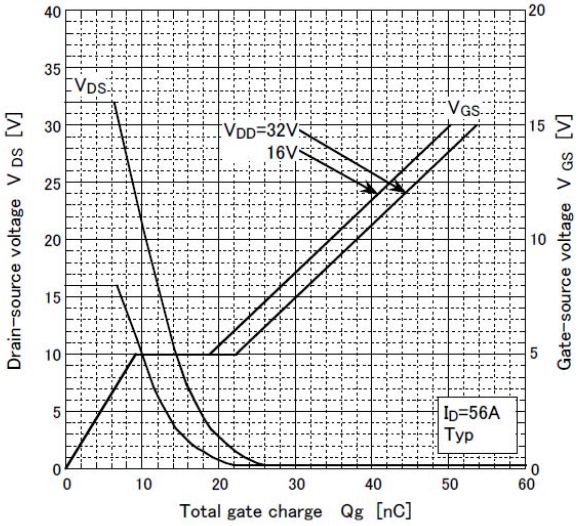
Capacitance characteristics



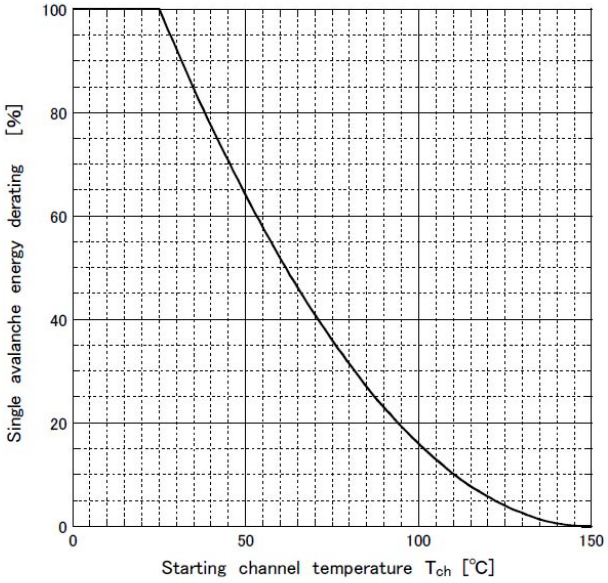
Power derating – case temperature



Gate charge characteristics



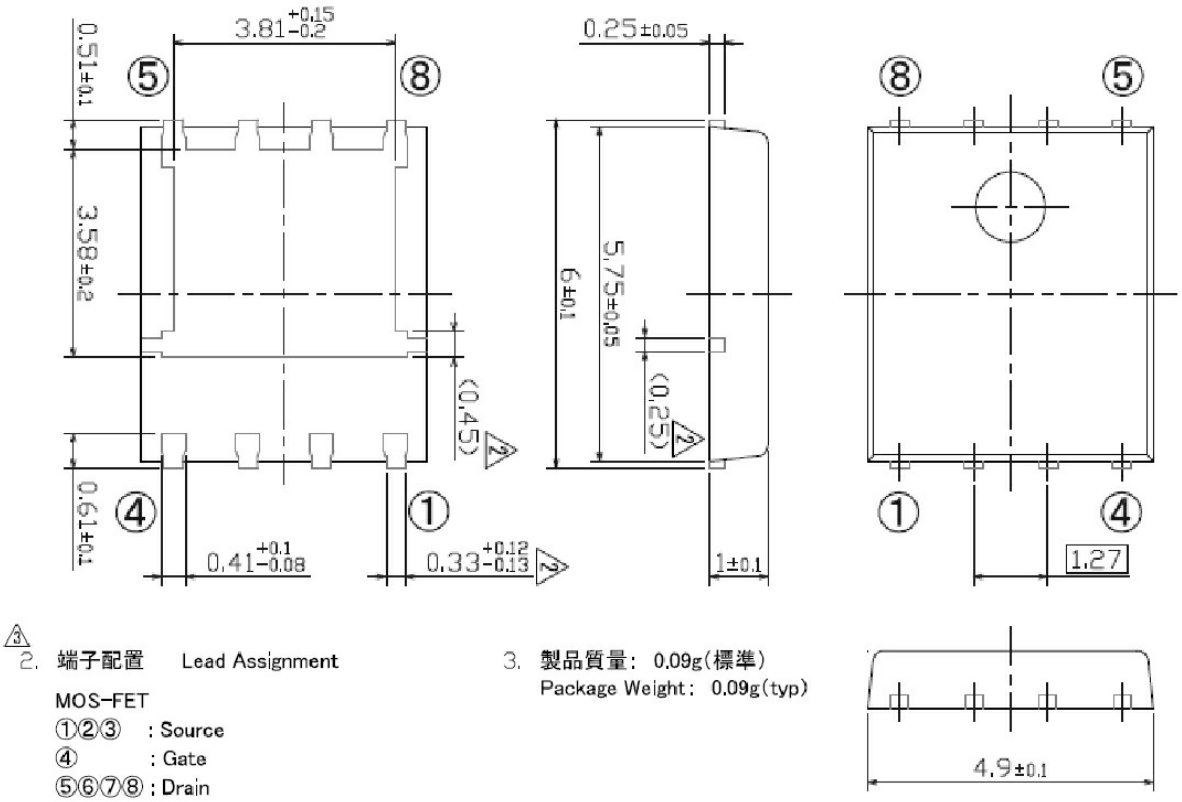
Single avalanche energy derating
vs channel temperature



Outline Dimensions

unit:mm

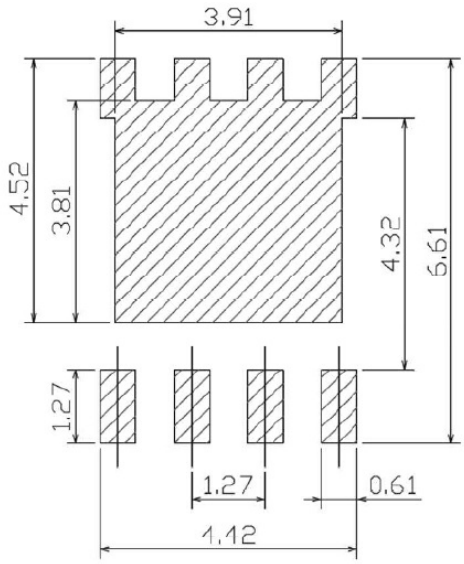
UNIT: mm



2. 端子配置　Lead Assignment

MOS-FET
①②③　: Source
④　: Gate
⑤⑥⑦⑧ : Drain

3. 製品質量：0.09g(標準)
Package Weight：0.09g(typ)



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